

## **PN4250A**



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## **PNP General Purpose Amplifier**

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 300 mA. Sourced from Process 68. See PN200 for characteristics.

### **Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	60	V
Vсво	Collector-Base Voltage	60	V
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V
lc	Collector Current - Continuous	500	mA
TJ, Tstg	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

## NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## Thermal Characteristics

Thermal Characteristics     TA = 25°C unless otherwise noted					
Symbol	Characteristic	Мах	Units		
		PN4250A	_		
PD	Total Device Dissipation	625	mW		
	Derate above 25°C	5.0	mW/°C		
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W		
$R_{\theta_{JA}}$	Thermal Resistance, Junction to Ambient	200	°C/W		

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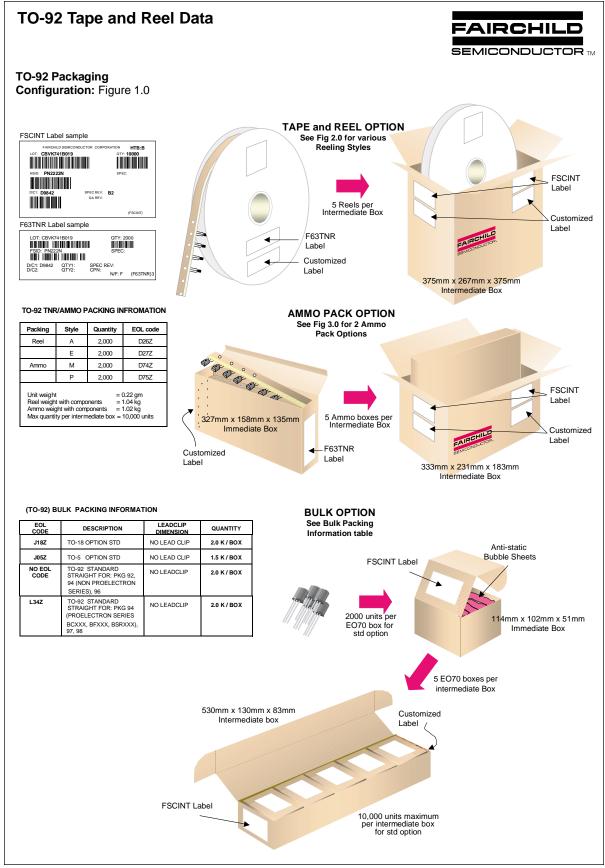
## PNP General Purpose Amplifier (continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 5.0 \text{ mA}, I_{\rm B} = 0$	60		V
V <sub>(BR)CES</sub>	Collector-Emitter Breakdown Voltage*	$I_{C} = 10 \ \mu A, \ I_{B} = 0$	60		V
V <sub>(BR)</sub> CBO	Collector-Base Breakdown Voltage	$I_{C} = 10 \ \mu A, I_{E} = 0$	60		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 10 \ \mu A, \ I_C = 0$	5.0		V
Ісво	Collector-Cutoff Current	$V_{CB} = 50 \text{ V}, I_E = 0$		10	nA
I <sub>EBO</sub>	Emitter-Cutoff Current	$V_{EB} = 3.0 \text{ V}, I_{C} = 0$		20	nA
	RACTERISTICS*		250	700	
	ACTERISTICS* DC Current Gain	$V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 100 \ \mu\text{A}$	250	700	
ON CHAF h <sub>FE</sub> V <sub>CE(sat)</sub>		$V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 100 \ \mu\text{A}$ I_C = 10 mA, I_B = 0.5 mA	250	700 0.25	V
h <sub>FE</sub> V <sub>CE(sat)</sub> SMALL S	DC Current Gain Collector-Emitter Saturation Voltage	Ic = 10 mA, I <sub>B</sub> = 0.5 mA	250	0.25	
h <sub>FE</sub> V <sub>CE(sat)</sub> SMALL S Cob	DC Current Gain Collector-Emitter Saturation Voltage IGNAL CHARACTERISTICS Output Capacitance	Ic = 10 mA, I <sub>B</sub> = 0.5 mA V <sub>CB</sub> = 5.0 V, f = 1.0 MHz		0.25 6.0	V PF
h <sub>FE</sub> V <sub>CE(sat)</sub> SMALL S Cob hfe	DC Current Gain Collector-Emitter Saturation Voltage IGNAL CHARACTERISTICS Output Capacitance Small-signal Current Gain	$I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA}$ $V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$ $V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA},$	250	6.0 800	pF
h <sub>FE</sub> V <sub>CE(sat)</sub> SMALL S C <sub>ob</sub> h <sub>fe</sub> h <sub>ie</sub>	DC Current Gain Collector-Emitter Saturation Voltage IGNAL CHARACTERISTICS Output Capacitance Small-signal Current Gain Input Impedance	Ic = 10 mA, I <sub>B</sub> = 0.5 mA V <sub>CB</sub> = 5.0 V, f = 1.0 MHz	250 6.0	6.0 800 20	pF kΩ
h <sub>FE</sub> V <sub>CE(sat)</sub> SMALL S Cob hfe hie hoe	DC Current Gain Collector-Emitter Saturation Voltage IGNAL CHARACTERISTICS Output Capacitance Small-signal Current Gain Input Impedance Output Admittance	$I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA}$ $V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$ $V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA},$	250	6.0 800 20 50	pF kΩ μmhos
h <sub>FE</sub> V <sub>CE(sat)</sub> SMALL S Cob híre hire	DC Current Gain Collector-Emitter Saturation Voltage IGNAL CHARACTERISTICS Output Capacitance Small-signal Current Gain Input Impedance	$I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA}$ $V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$ $V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA},$	250 6.0	6.0 800 20	pF

\*Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%

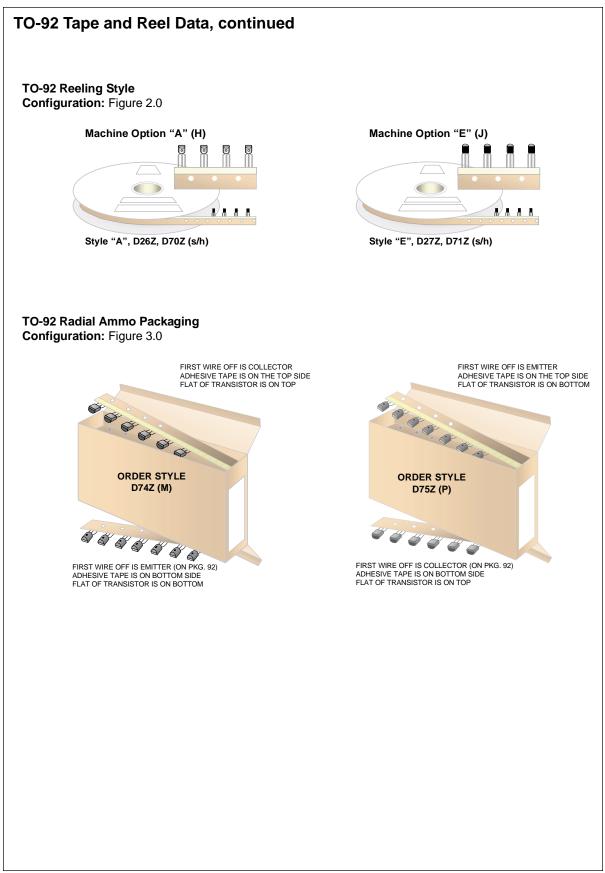
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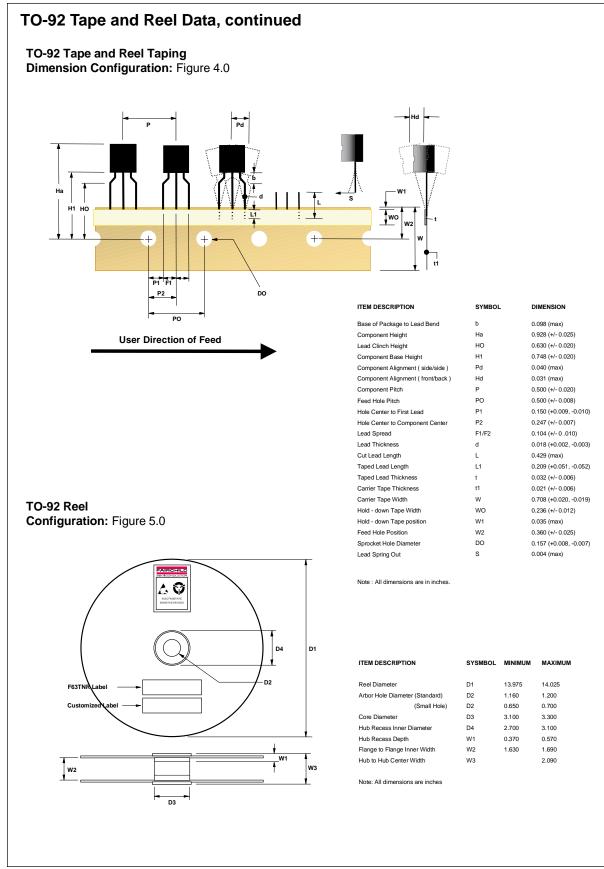


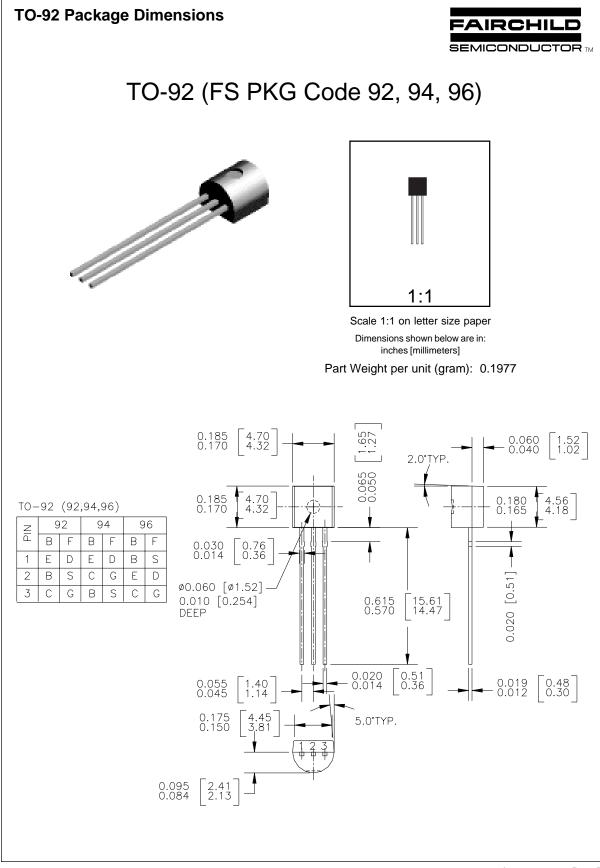
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March 2001, Rev. B1



September 1999, Rev. B





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